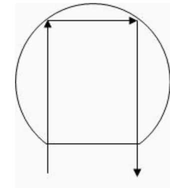
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	200.00 +/- 0.50 mm	WaferVendor
	2.0	Notch or Flat	Notch	Wafer Vendor
	3.0	Notch Direction	{110}+/-1 degree	Wafer Vendor
	4.0	Growth Method	CZ	Wafer Vendor
	5.0	Type	P	Wafer Vendor
	6.0	Dopant	Boron	Wafer Vendor
	7.0	Resistivity	5- 100 Ohm-cm	Wafer Vendor
	8.0	Overall Thickness	380.00 +/- 5.00 um	ADE 100% SEMI MF533
	9.0	Total Thickness Variation (TTV)	<3.00um	ADE 100% SEMI MF1530
	10.0	Bow	<50.00um	ADE 100% SEMI MF1390
	11.0	Warp	<50.00um	ADE 100% SEMI MF1390
	12.0	Lasermarking	On wafer FRONTSIDE next to notch, as per attachment. Scribe format: [ICE-380.XXXX] (unique scribe)	Guaranteed by process
	13.0	Orientation	<100> +/-0.5	Wafer Vendor
	14.0	Back Surface Quality	Polished.	Wafer Vendor
	15.0	Front Surface Quality	Prime	Wafer Vendor
	16.0	Edge Chips	None	Bright Light 100% (note 2)
HandleSilicon	17.0	Handle Thickness	380.00 +/- 5.00 um	ADE 100% SEMI MF533
	18.0	Surface Haze	None	Bright Light, 100% (note 2).
	19.0	Total scratch length	None	Bright Light, 100% (note 2).

Part Number	Customer		
Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 200.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

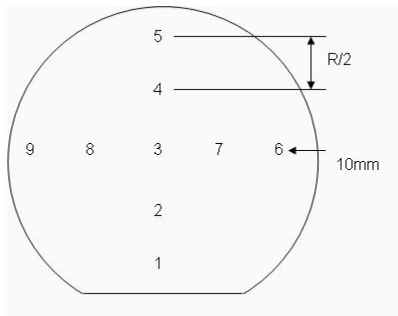
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information